

# N-Channel 30-V (D-S) MOSFET

PRODUC	CT SUMMARY		
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
30	0.0048 at V <sub>GS</sub> = 10 V	26	26.5 nC
30	0.006 at V <sub>GS</sub> = 4.5 V	23.3	20.5 110

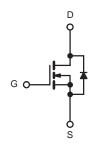
#### **FEATURES**

- DT-Trench Power MOSFET
- 100 %  $R_g$  and UIS Tested



#### **APPLICATIONS**

- DC/DC Conversion
  - Low-Side Switch
- Notebook PC
- Gaming



N-Channel MOSFET

PowerPAK SO-8
6.15 mm 5.15 mm 2 3 4 6
Bottom View

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	30	V	
Gate-Source Voltage		$V_{GS}$	± 20	V	
	T <sub>C</sub> = 25 °C		26		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 70 °C	l <sub>D</sub>	22.6		
commode Prairi current (1) = 100 °C)	T <sub>A</sub> = 25 °C	J 0.	21.5 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C		17.1 <sup>b, c</sup>	Α .	
Pulsed Drain Current		I <sub>DM</sub>	70	^	
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	I <sub>S</sub>	5.4		
Continuous Godice-Diam Diode Current	T <sub>A</sub> = 25 °C	'S	2.7 <sup>b, c</sup>		
Single Pulse Avalanche Current  L = 0.1 mH		I <sub>AS</sub>	40		
Avalanche Energy		E <sub>AS</sub>	80	mJ	
	T <sub>C</sub> = 25 °C		6.0		
Maximum Power Dissipation	T <sub>C</sub> = 70 °C	$P_{D}$	3.3	w	
Maximum i ower bissipation	T <sub>A</sub> = 25 °C	] '' [	3.0 <sup>b, c</sup>	V V	
	T <sub>A</sub> = 70 °C	1	1.9 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stq</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RA	TINGS				
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	t ≤ 10 s	R <sub>thJA</sub>	33	42	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	16	21	C/ VV

#### Notes:

- a. Based on  $T_C = 25$  °C.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. Maximum under Steady State conditions is 85 °C/W.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	<u> </u>		•		•	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V, } I_D = 1 \text{ mA}$	30			V
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	1 250		27		\//00
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	- I <sub>D</sub> = 250 μA		- 5.6		mV/°(
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	1.2		2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α
	Б	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A		0.0036	0.0048	Ω
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$		0.0052	0.0060	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A		75		S
Dynamic <sup>b</sup>	l					
Input Capacitance	C <sub>iss</sub>			3545		
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		650		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			240		
Total Gate Charge	$Q_g$	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A		62	95	
				26.5	40	0
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 10 \text{ A}$		8.5		nC
Gate-Drain Charge	Q <sub>gd</sub>			7.3		
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.2	1.1	2.2	Ω
Turn-On Delay Time	t <sub>d(on)</sub>			35	60	
Rise Time	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, R_{L} = 1.5 \Omega$		16	30	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		48	85	
Fall Time	t <sub>f</sub>			16	30	20
Turn-On Delay Time	t <sub>d(on)</sub>			18	35	ns
Rise Time	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, R_{L} = 1.5 \Omega$		8	16	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		41	75	
Fall Time	t <sub>f</sub>			8	18	
<b>Drain-Source Body Diode Characterist</b>	ics					
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			26	۸
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				70	Α
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 3 A		0.72	1.1	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>			33	65	ns
Body Diode Reverse Recovery Charge	covery Charge O			27	54	nC
Reverse Recovery Fall Time	t <sub>a</sub>	$I_F = 10 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 \text{ °C}$		17		
Reverse Recovery Rise Time	t <sub>b</sub>			16		ns

### Notes:

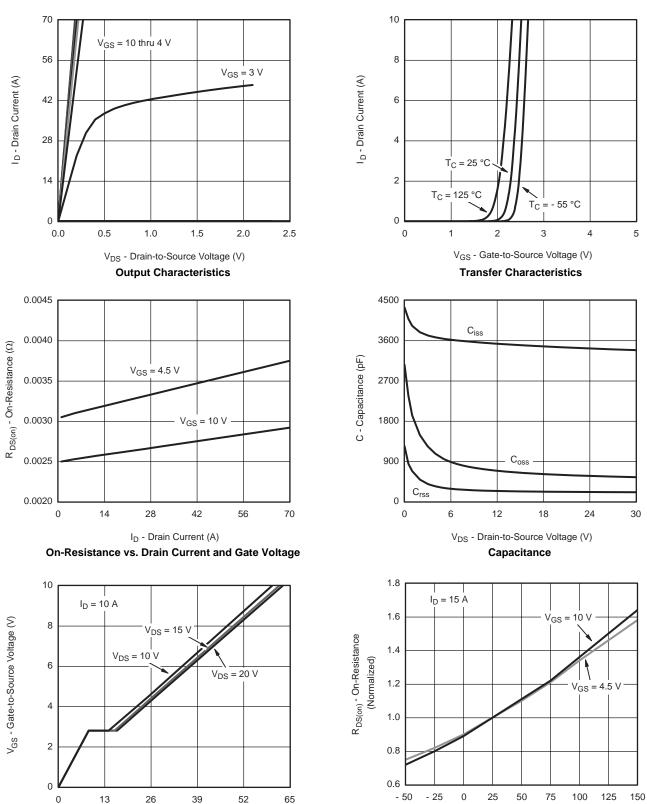
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 % b. Guaranteed by design, not subject to production testing.



### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

 $\mathbf{Q}_{g}$  - Total Gate Charge (nC)  $\mathbf{Gate\ Charge}$ 

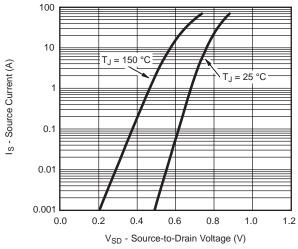


T<sub>J</sub> - Junction Temperature (°C)

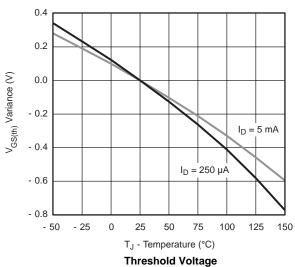
On-Resistance vs. Junction Temperature

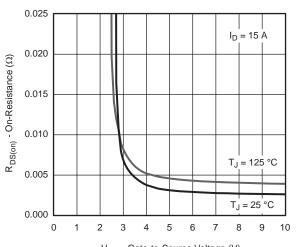


### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

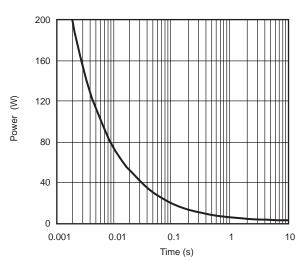


#### Source-Drain Diode Forward Voltage

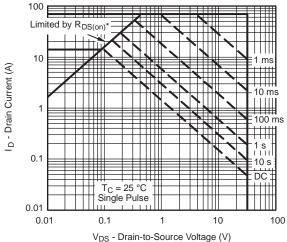




V<sub>GS</sub> - Gate-to-Source Voltage (V) On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power

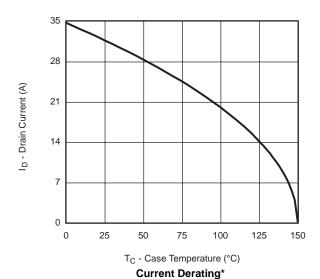


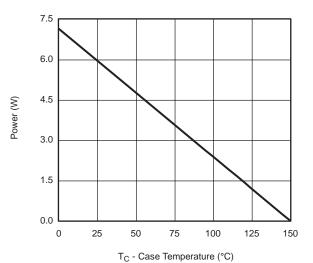
\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

Safe Operating Area, Junction-to-Ambient

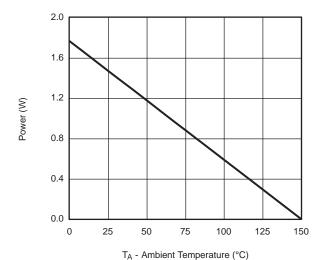


### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Power Derating, Junction-to-Foot

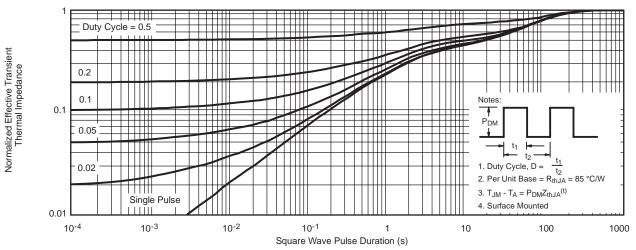


Power, Junction-to-Ambient

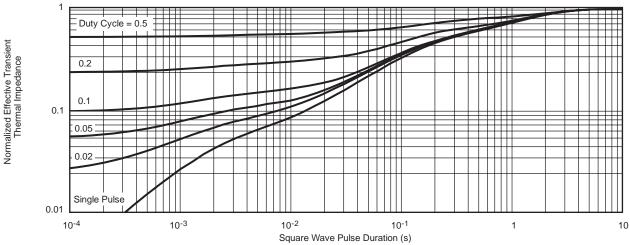
<sup>\*</sup> The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



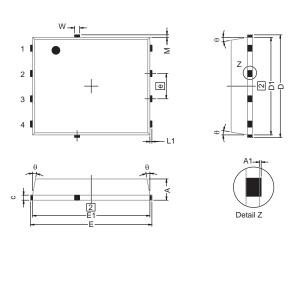
Normalized Thermal Transient Impedance, Junction-to-Ambient

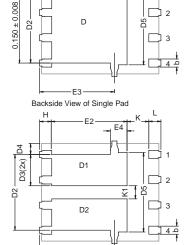


Normalized Thermal Transient Impedance, Junction-to-Foot



### PowerPAK SO-8, (SINGLE/DUAL)





### Notes

- 1. Inch will govern.
- 2 Dimensions exclusive of mold gate burrs.
- 3. Dimensions exclusive of mold flash and cutting burrs.

	-E3	
Rackeide	View of D	ual Pad

		MILLIMETERS			INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.97	1.04	1.12	0.038	0.041	0.044	
A1	0.00	-	0.05	0.000	=	0.002	
b	0.33	0.41	0.51	0.013	0.016	0.020	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	5.05	5.15	5.26	0.199	0.203	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.56	3.76	3.91	0.140	0.148	0.154	
D3	1.32	1.50	1.68	0.052	0.059	0.066	
D4		0.57 TYP.		0.0225 TYP.			
D5		3.98 TYP.			0.157 TYP.		
Е	6.05	6.15	6.25	0.238	0.242	0.246	
E1	5.79	5.89	5.99	0.228	0.232	0.236	
E2	3.48	3.66	3.84	0.137	0.144	0.151	
E3	3.68	3.78	3.91	0.145	0.149	0.154	
E4	0.75 TYP.			0.030 TYP.			
е		1.27 BSC			0.050 BSC		
K		1.27 TYP.		0.050 TYP.			
K1	0.56	-	-	0.022	=	-	
Н	0.51	0.61	0.71	0.020	0.024	0.028	
L	0.51	0.61	0.71	0.020	0.024	0.028	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
М	0.125 TYP. 0.005 TYP.						

ECN: T10-0055-Rev. J, 15-Feb-10

DWG: 5881





### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Din-Tek Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Din-Tek"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Din-Tek makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Din-Tek disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Din-Tek's knowledge of typical requirements that are often placed on Din-Tek products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Din-Tek's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Din-Tek products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Din-Tek product could result in personal injury or death. Customers using or selling Din-Tek products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Din-Tek personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Din-Tek. Product names and markings noted herein may be trademarks of their respective owners.

# **Material Category Policy**

Din-Tek Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Din-Tek documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Din-Tek Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Din-Tek documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.